

May 1999

LM6161/LM6261/LM6361 **High Speed Operational Amplifier**

General Description

The LM6161 family of high-speed amplifiers exhibits an excellent speed-power product in delivering 300 V/µs and 50 MHz unity gain stability with only 5 mA of supply current. Further power savings and application convenience are possible by taking advantage of the wide dynamic range in operating supply voltage which extends all the way down to +5V.

These amplifiers are built with National's VIP™ (Vertically Integrated PNP) process which provides fast PNP transistors that are true complements to the already fast NPN devices. This advanced junction-isolated process delivers high speed performance without the need for complex and expensive dielectric isolation.

Features

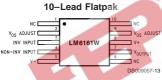
■ High slew rate 300 V/µs

- High unity gain freq 50 MHz
- Low supply current 5 mA
- Fast settling 120 ns to 0.1%
- Low differential gain <0.1%
- Low differential phase 0.1°
- Wide supply range 4.75V to 32V
- Stable with unlimited capacitive load
- Well behaved; easy to apply

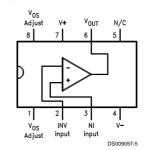
Applications

- Video amplifier
- High-frequency filter
- Wide-bandwidth signal conditioning
- Radar
- Sonar

Connection Diagrams



See NS Package Number W10A



See NS Package Number J08A, N08E or M08A

	Package	NSC		
Military	Industrial Commercial			Drawing
-55°C ≤ T _A ≤ +125°C	-25°C ≤ T _A ≤ +85°C	0° C \leq T _A \leq +70 $^{\circ}$ C		
	LM6261N	LM6361N	8-Pin	N08E
			Molded DIP	
LM6161J/883		LM6361J	8-Pin	J08A
5962-8962101PA			Ceramic DIP	
	LM6261M	LM6361M	8-Pin Molded	M08A
			Surface Mt.	
LM6161WG/883			10-Lead	WG10A
5962-8962101XA			Ceramic SOIC	
LM6161W/883			10-Pin	W10A
5962-8962101HA			Ceramic Flatpak	

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Absolute Maximum Ratings (Note 12)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V+ - V-) 36V

Differential Input Voltage

±8V

Common-Mode Voltage Range

(Note 10) $(V^+ - 0.7V)$ to $(V^- + 0.7V)$

Output Short Circuit to GND (Note 1)

Soldering Information Dual-In-Line Package (N, J) Soldering (10 sec.)

Small Outline Package (M) Vapor Phase (60 sec.) Infrared (15 sec.)

215°C 220°C

260°C

Continuous

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

–65°C to +150°C Storage Temp Range Max Junction Temperature 150°C ESD Tolerance (Notes 6, 7) ±700V

Operating Ratings (Note 12)

Temperature Range (Note 2)

LM6161 $-55^{\circ}C \leq T_{J} \leq +125^{\circ}C$ LM6261 $-25^{\circ}C \leq T_{J} \leq +85^{\circ}C$ $0^{\circ}\text{C} \le \text{T}_{\text{J}} \le +70^{\circ}\text{C}$ LM6361

4.75V to 32V Supply Voltage Range

DC Electrical Characteristics

The following specifications apply for Supply Voltage = $\pm 15 \text{V}$, V_{CM} = 0, $\text{R}_{\text{L}} \geq 100 \text{ k}\Omega$ and R_{S} = 50Ω unless otherwise noted. **Boldface** limits apply for $\text{T}_{\text{J}} = \text{T}_{\text{MIN}}$ to T_{MAX} ; all other limits $\text{T}_{\text{J}} = 25\,^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Тур	LM6161	LM6261	LM6361	Units
			a	1 Limit	Limit	Limit	1
			20 1	(Notes 3, 11)	(Note 3)	(Note 3)	
Vos	Input Offset Voltage		5	7	7	20	mV
			C	10	9	22	Max
Vos	Input Offset Voltage		10				μV/°C
Drift	Average Drift		1				
I _b	Input Bias Current		2	3	3	5	μA
				6	5	6	Max
los	Input Offset Current		150	350	350	1500	nA
				800	600	1900	Max
los	Input Offset Current		0.4				nA/°C
Drift	Average Drift						
R _{IN}	Input Resistance	Differential	325				kΩ
C _{IN}	Input Capacitance	A _V = +1 @ 10 MHz	1.5				pF
A_{VOL}	Large Signal	$V_{OUT} = \pm 10V$,	750	550	550	400	V/V
Volta	Voltage Gain	$R_L = 2 k\Omega \text{ (Note 9)}$		300	400	350	Min
		$R_L = 10 \text{ k}\Omega \text{ (Note 9)}$	2900				V/V
V_{CM}	Input Common-Mode	Supply = $\pm 15V$	+14.0	+13.9	+13.9	+13.8	Volts
	Voltage Range			+13.8	+13.8	+13.7	Min
			-13.2	-12.9	-12.9	-12.8	Volts
				-12.7	-12.7	-12.7	Min
		Supply = +5V	4.0	3.9	3.9	3.8	Volts
		(Note 4)		3.8	3.8	3.7	Min
			1.8	2.0	2.0	2.1	Volts
				2.2	2.2	2.2	Max
CMRR	Common-Mode	-10V ≤ V _{CM} ≤ +10V	94	80	80	72	dB
	Rejection Ratio			74	76	70	Min
PSRR	Power Supply	$\pm 10 \text{V} \le \text{V}^{\pm} \le \pm 16 \text{V}$	90	80	80	72	dB
	Rejection Ratio			74	76	70	Min

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DC Electrical Characteristics (Continued)

The following specifications apply for Supply Voltage = ± 15 V, V_{CM} = 0, $R_L \ge 100$ k Ω and R_S = 50Ω unless otherwise noted. **Boldface** limits apply for $T_J = T_{MIN}$ to T_{MAX} ; all other limits $T_J = 25^{\circ}C$.

Symbol	Parameter	Conditions	Тур	LM6161	LM6261	LM6361	Units
				Limit	Limit	Limit	
				(Notes 3, 11)	(Note 3)	(Note 3)	
Vo	Output Voltage	Supply = ±15V	+14.2	+13.5	+13.5	+13.4	Volts
	Swing	and $R_L = 2 k\Omega$		+13.3	+13.3	+13.3	Min
			-13.4	-13.0	-13.0	-12.9	Volts
				-12.7	-12.8	-12.8	Min
		Supply = +5V	4.2	3.5	3.5	3.4	Volts
		and $R_L = 2 k\Omega$		3.3	3.3	3.3	Min
		(Note 4)	1.3	1.7	1.7	1.8	Volts
				2.0	1.9	1.9	Max
	Output Short	Source	65	30	30	30	mA
Circuit	Circuit Current			20	25	25	Min
		Sink	65	30	30	30	mA
				20	25	25	Min
Is	Supply Current		5.0	6.5	6.5	6.8	mA
				6.8	6.7	6.9	Max

AC Electrical Characteristics

The following specifications apply for Supply Voltage = ± 15 V, V_{CM} = 0, $R_L \ge 100~k\Omega$ and R_S = 50Ω unless otherwise noted. Boldface limits apply for T_J = T_{MIN} to T_{MAX} ; all other limits T_J = 25°C.

				LM6161	LM6261	LM6361	
Symbol	Parameter	Conditions	Тур	Limit	Limit	Limit	Units
				(Notes 3, 11)	(Note 3)	(Note 3)	
GBW	Gain-Bandwidth	@ f = 20 MHz	50	40	40	35	MHz
	Product			30	35	32	Min
		Supply = ±5V	35				MHz
SR	Slew Rate	$A_V = +1 \text{ (Note 8)}$	300	200	200	200	V/µs
				180	180	180	Min
		Supply = ±5V (Note 8)	200				V/µs
PBW	Power Bandwidth	V _{OUT} = 20 V _{PP}	4.5				MHz
t _S	Settling Time	10V Step to 0.1%	120				ns
		$A_V = -1$, $R_L = 2 \text{ k}\Omega$					
φm	Phase Margin		45				Deg
A _D	Differential Gain	NTSC, A _V = +4	<0.1				%
φD	Differential Phase	NTSC, A _V = +4	0.1				Deg
e _{np-p}	Input Noise Voltage	f = 10 kHz	15				nV/√Hz
i _{np-p}	Input Noise Current	f = 10 kHz	1.5				pA/√ Hz

Note 1: Continuous short-circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.

Note 2: The typical junction-to-ambient thermal resistance of the molded plastic DIP (N) is 105°C/W, the molded plastic SO (M) package is 155°C/W, and the cerdip (J) package is 125°C/W. All numbers apply for packages soldered directly into a printed circuit board.

Note 3: Limits are guaranteed by testing or correlation.

Note 4: For single supply operation, the following conditions apply: V⁺ = 5V, V⁻ = 0V, V_{CM} = 2.5V, V_{OUT} = 2.5V. Pin 1 & Pin 8 (Vos Adjust) are each connected to Pin 4 (V⁻) to realize maximum output swing. This connection will degrade V_{OS}, V_{OS} Drift, and Input Voltage Noise

Note 6: In order to achieve optimum AC performance, the input stage was designed without protective clamps. Exceeding the maximum differential input voltage results in reverse breakdown of the base-emitter junction of one of the input transistors and probable degradation of the input parameters (especially Vos, los, and Noise).

AC Electrical Characteristics (Continued)

Note 7: The average voltage that the weakest pin combinations (those involving Pin 2 or Pin 3) can withstand and still conform to the datasheet limits. The test circuit used consists of the human body model of 100 pF in series with 1500Ω.

Note 8: V_{IN} = 8V step. For supply = ±5V, V_{IN} = 5V step.

Note 9: Voltage Gain is the total output swing (20V) divided by the input signal required to produce that swing.

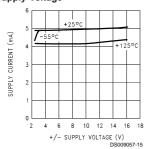
Note 10: The voltage between V^{+} and either input pin must not exceed 36V.

Note 11: A military RETS electrical test specification is available on request. At the time of printing, the RETS6161X specs complied with all Boldface limits in this

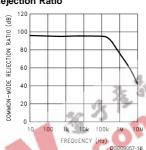
Note 12: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

Typical Performance Characteristics (R_L = 10 k Ω , T_A = 25°C unless otherwise specified)

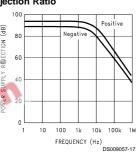
Supply Current vs Supply Voltage



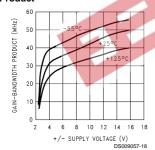
Common-Mode Rejection Ratio



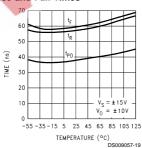
Power Supply Rejection Ratio



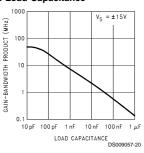
Gain-Bandwidth Product



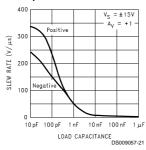
Propagation Delay Rise and Fall Times



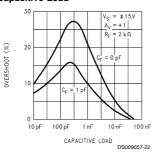
Gain-Bandwidth Product vs Load Capacitance



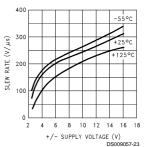
Slew Rate vs Load Capacitance



Overshoot vs Capacitive Load

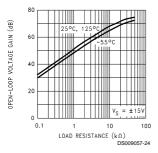


Slew Rate

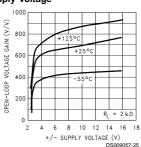


Typical Performance Characteristics (R $_L$ = 10 k $\Omega,\ T_A$ = 25 °C unless otherwise specified) (Continued)

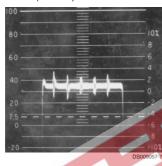
Voltage Gain vs Load Resistance



Gain vs Supply Voltage



Differential Gain (Note 13)

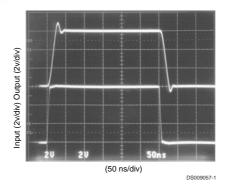


Differential Phase (Note 13)



Note 13: Differential gain and differential phase measured for four series LM6361 op amps configured as unity-gain followers, in series with an LM6321 buffer. Error added by LM6321 is negligible. Test performed using Tektronix Type 520 NTSC test system.

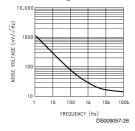
Step Response; Av = +1



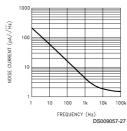
Typical Performance Characteristics (R_L = 10 k Ω , T_A = 25°C unless otherwise

specified) (Continued)

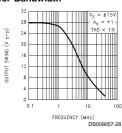
Input Noise Voltage



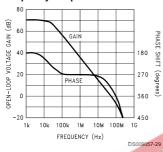
Input Noise Current



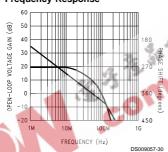
Power Bandwidth



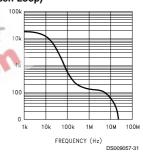
Open-Loop Frequency Response



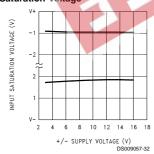
Open-Loop Frequency Response



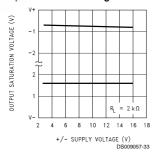
Output Impedence (Open-Loop)



Common-Mode Input Saturation Voltage

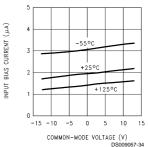


Output Saturation Voltage

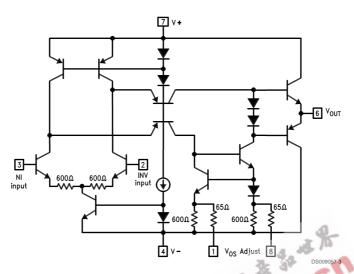


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Bias Current vs Common-Mode Voltage



Simplified Schematic



Applications Tips

The LM6361 has been compensated for unity-gain operation. Since this compensation involved adding emitter-degeneration resistors to the op amp's input stage, the open-loop gain was reduced as the stability increased. Gain error due to reduced A_{VOL} is most apparent at high gains; thus, for gains between 5 and 25, the less-compensated LM6364 should be used, and the uncompensated LM6365 is appropriate for gains of 25 or more. The LM6361, LM6364, and LM6365 have the same high slew rate, regardless of their compensation.

The LM6361 is unusually tolerant of capacitive loads. Most op amps tend to oscillate when their load capacitance is greater than about 200 pF (especially in low-gain circuits). The LM6361's compensation is effectively increased with load capacitance, reducing its bandwidth and increasing its stability.

Power supply bypassing is not as critical for the LM6361 as it is for other op amps in its speed class. Bypassing will, how-

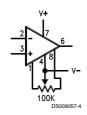
ever, improve the stability and transient response and is recommended for every design. 0.01 μF to 0.1 μF ceramic capacitors should be used (from each supply "rail" to ground); if the device is far away from its power supply source, an additional 2.2 μF to 10 μF of tantalum may provide extra noise reduction.

Keep all leads short to reduce stray capacitance and lead inductance, and make sure ground paths are low-impedance, especially where heavier currents will be flowing. Stray capacitance in the circuit layout can cause signal coupling across adjacent nodes and can cause gain to unintentionally vary with frequency.

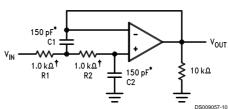
Breadboarded circuits will work best if they are built using generic PC boards with a good ground plane. If the op amps are used with sockets, as opposed to being soldered into the circuit, the additional input capacitance may degrade circuit performance.

Typical Applications

Offset Voltage Adjustment

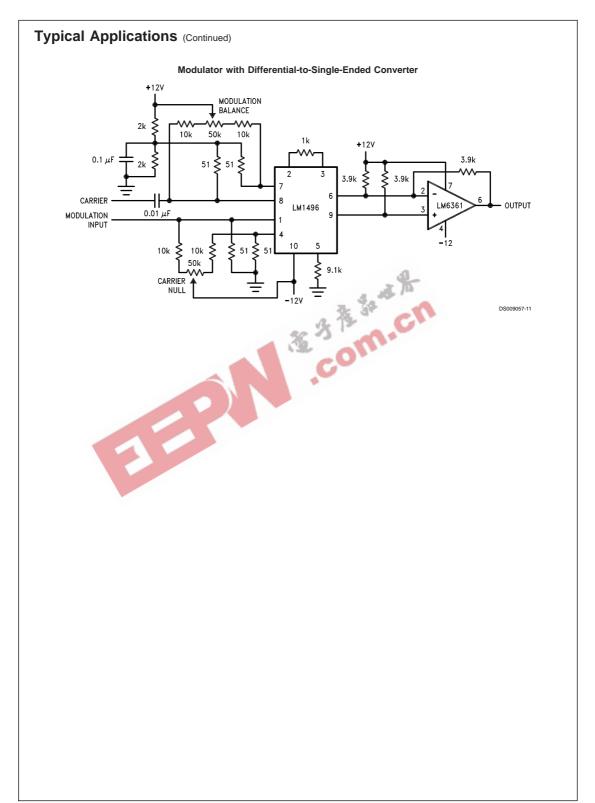


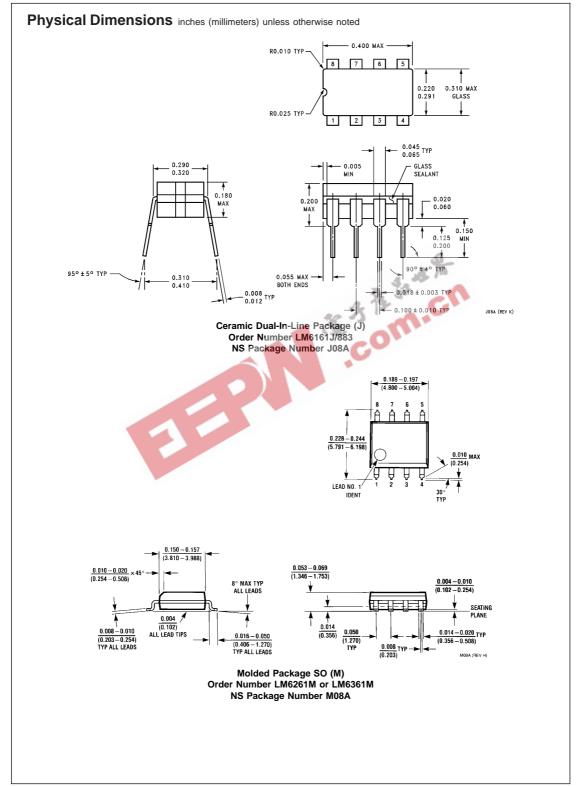
1 MHz Low-Pass Filter

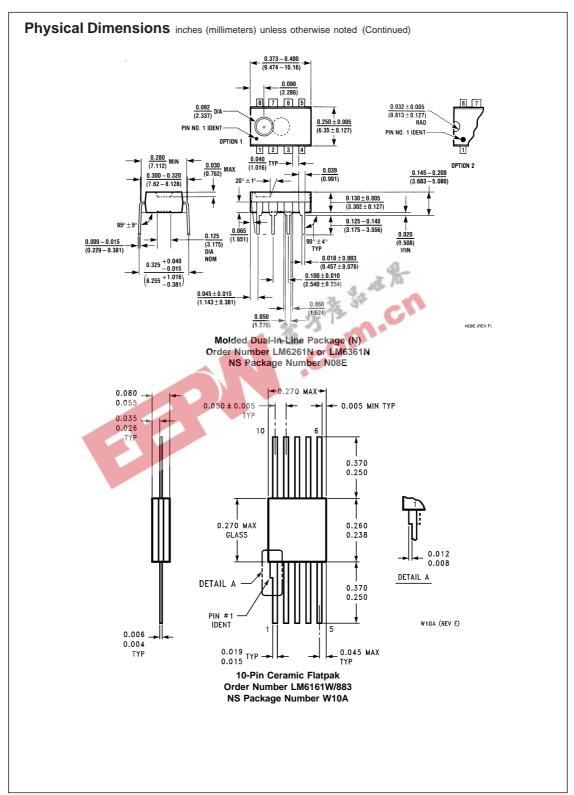


- †1% tolerance
- *Matching determines filter precision
- $f_{c} = (2\pi \sqrt{(R1 R2 C1 C2)})^{-1}$

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Notes



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Corporation
Americas
Tel: 1-800-272-9959 Fax: 1-800-737-7018 Email: support@nsc.com

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National Semiconductor
Europe
Fax: +49 (0) 1 80-530 85 86
Email: europe.support@nsc.com
Deutsch Tel: +49 (0) 1 80-530 85 85
English Tel: +49 (0) 1 80-532 78 32
Français Tel: +49 (0) 180-532 93 88
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